

Supplementary Materials

Electrochemical Etching-Assisted Fabrication of Quantum Tunneling Sensing Probes with Controlled Nanogap Width

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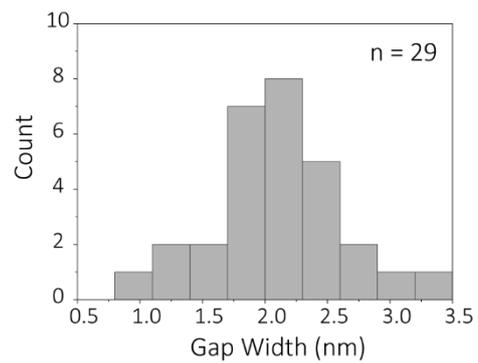


Figure S1. Histogram of gap width distribution for etched-tunneling electrodes.

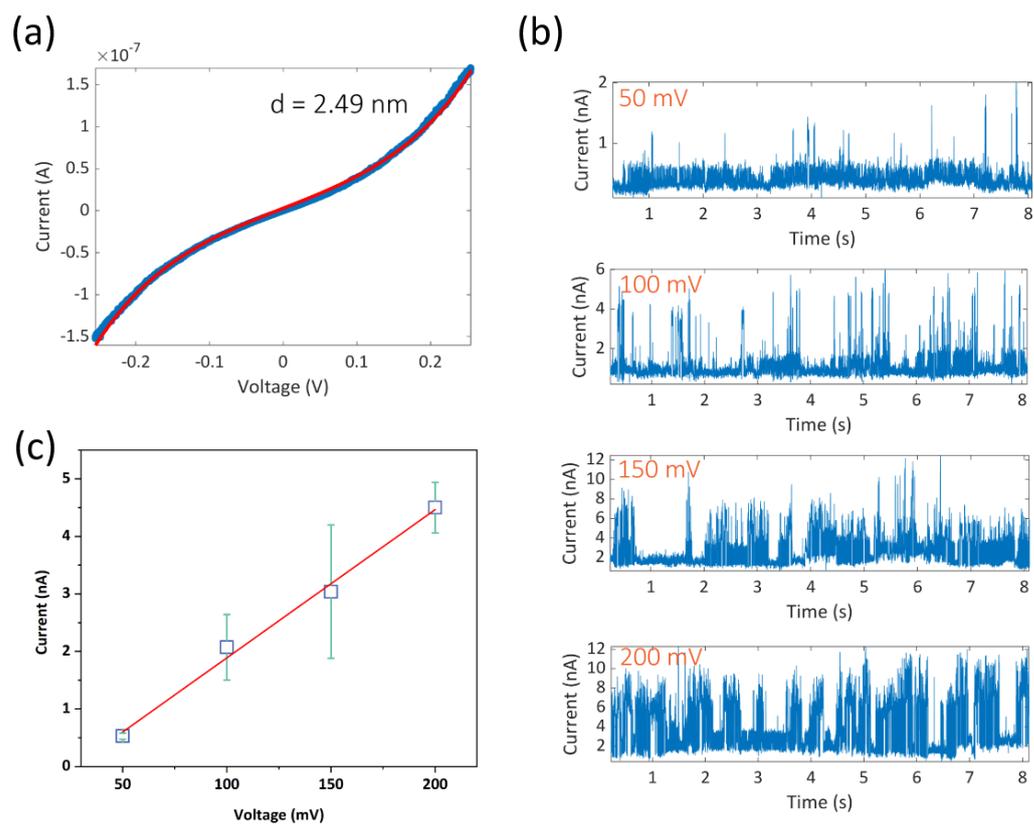


Figure S2. Tunneling current measurement of GOD under different bias voltage. (a) Tunneling current measurement of the used tunneling electrode and corresponding fit obtained by Simmons model. (b) Representative tunneling current-time trace under different bias voltage for 10 nmol/L GOD in 0.01 mol/L PBS solution (pH 7.4). (c) Plots of peak current versus bias voltage for data presented in (b). All error bars represent 1 standard deviation from the mean.